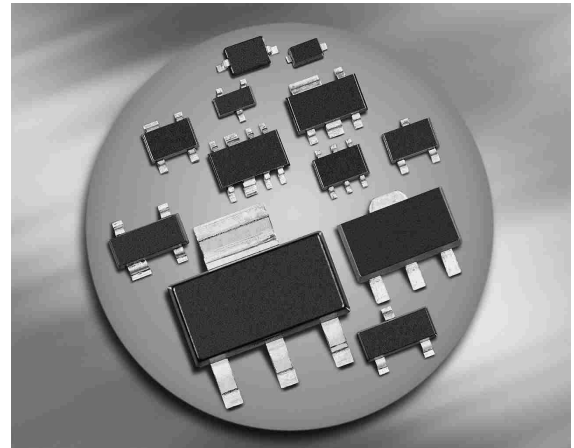
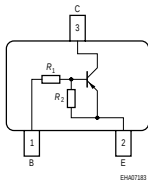


PNP Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1 = 22\text{ k}\Omega$, $R_2 = 22\text{ k}\Omega$)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



BCR191 BCR191W



Type	Marking	Pin Configuration						Package
BCR191	WOs	1=B	2=E	3=C	-	-	-	SOT23
BCR191W	WOs	1=B	2=E	3=C	-	-	-	SOT323

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	60	
Input reverse voltage	$V_{i(rev)}$	10	
Collector current	I_C	100	mA
Total power dissipation- BCR191, $T_S \leq 102^\circ\text{C}$ BCR191W, $T_S \leq 124^\circ\text{C}$	P_{tot}	200 250	mW
Junction temperature	T_j	150	
Storage temperature	T_{stg}	-65 ... 150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BCR191		≤ 240	
BCR191W		≤ 105	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}$, $I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}$, $I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{ V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 10 \text{ V}$, $I_C = 0$	I_{EBO}	-	-	350	μA
DC current gain ²⁾ $I_C = 5 \text{ mA}$, $V_{CE} = 5 \text{ V}$	h_{FE}	50	-	-	-
Collector-emitter saturation voltage ²⁾ $I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}$, $V_{CE} = 5 \text{ V}$	$V_{i(off)}$	0.8	-	1.5	
Input on voltage $I_C = 2 \text{ mA}$, $V_{CE} = 0.3 \text{ V}$	$V_{i(on)}$	1	-	2.5	
Input resistor	R_1	15	22	29	k Ω
Resistor ratio	R_1/R_2	0.9	1	1.1	-

AC Characteristics

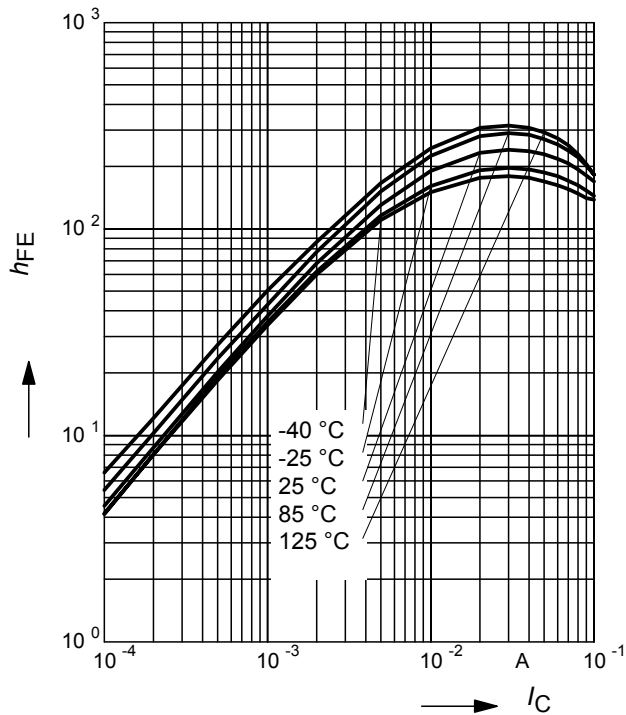
Transition frequency $I_C = 10 \text{ mA}$, $V_{CE} = 5 \text{ V}$, $f = 100 \text{ MHz}$	f_T	-	200	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{cb}	-	3	-	pF

¹⁾For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

²⁾Pulse test: $t < 300 \mu\text{s}$; $D < 2\%$

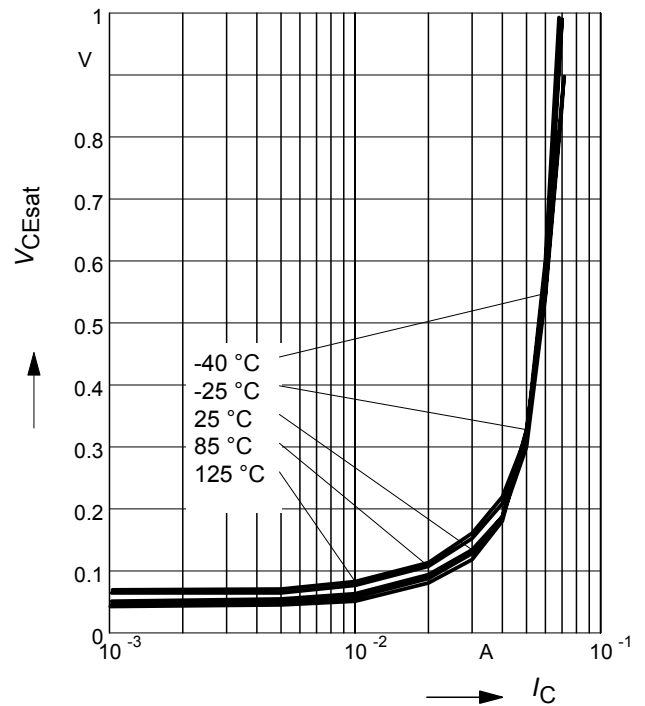
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5 \text{ V}$ (common emitter configuration)



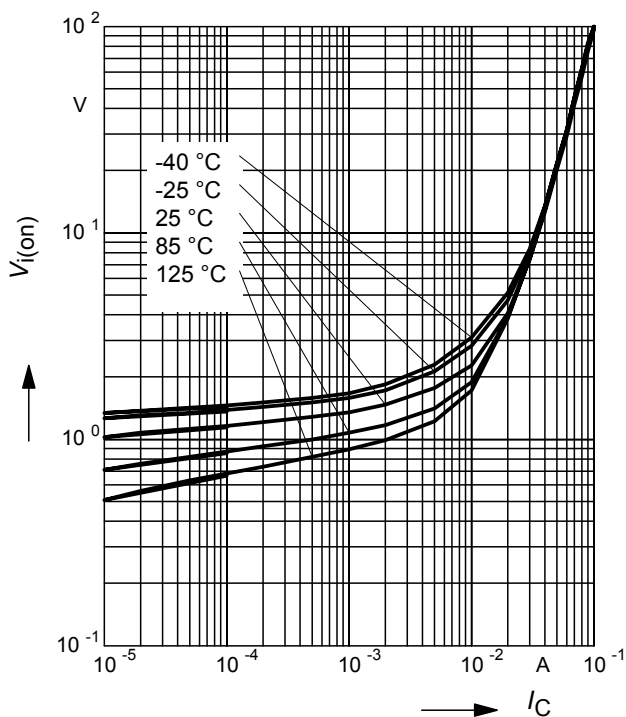
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C)$, $I_C/I_B = 20$



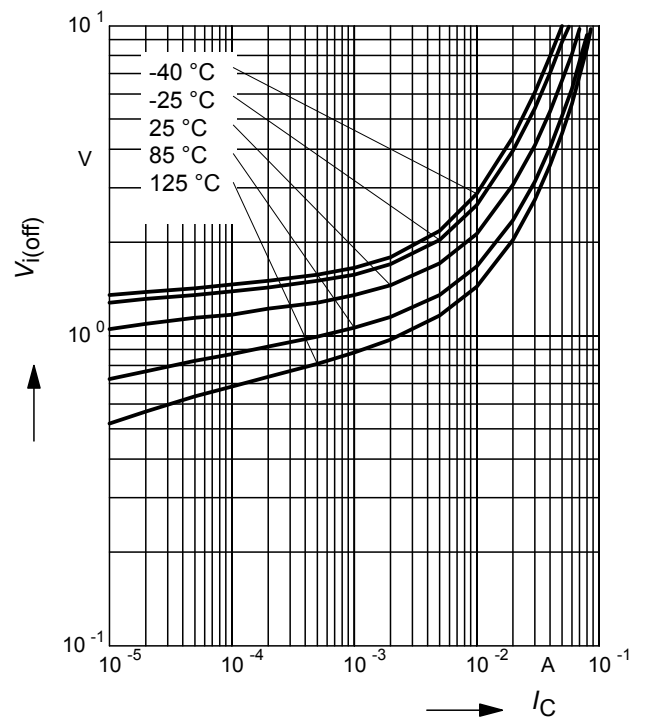
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3 \text{ V}$ (common emitter configuration)



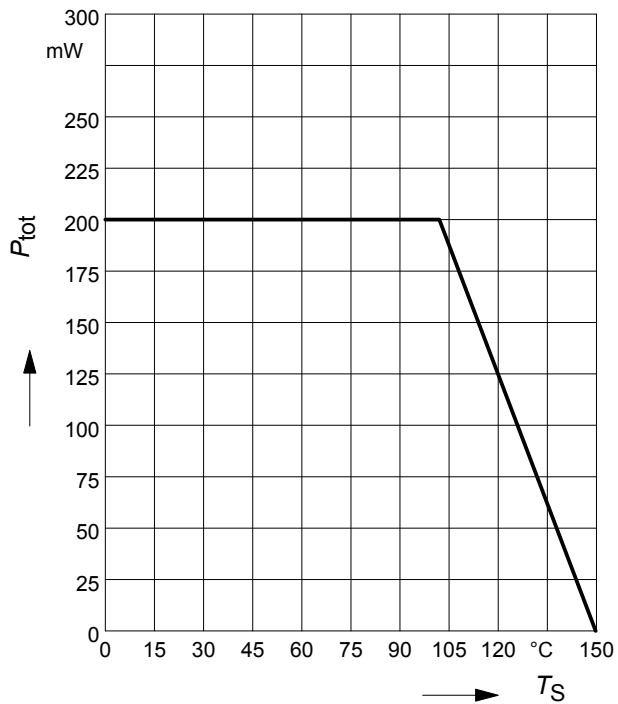
Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5 \text{ V}$ (common emitter configuration)



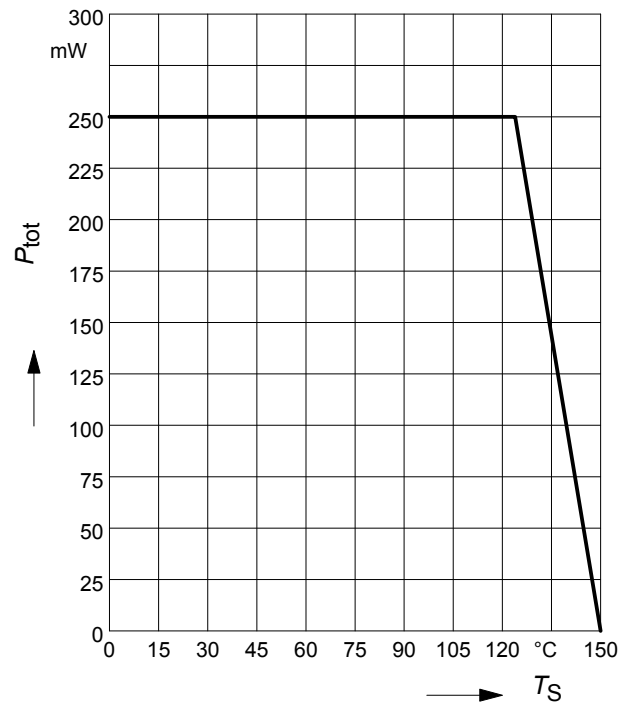
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR191



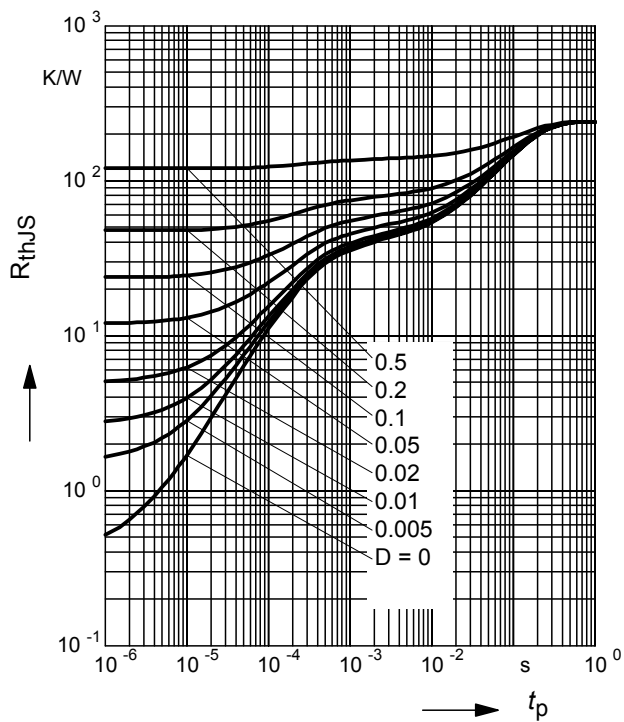
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR191W



Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$

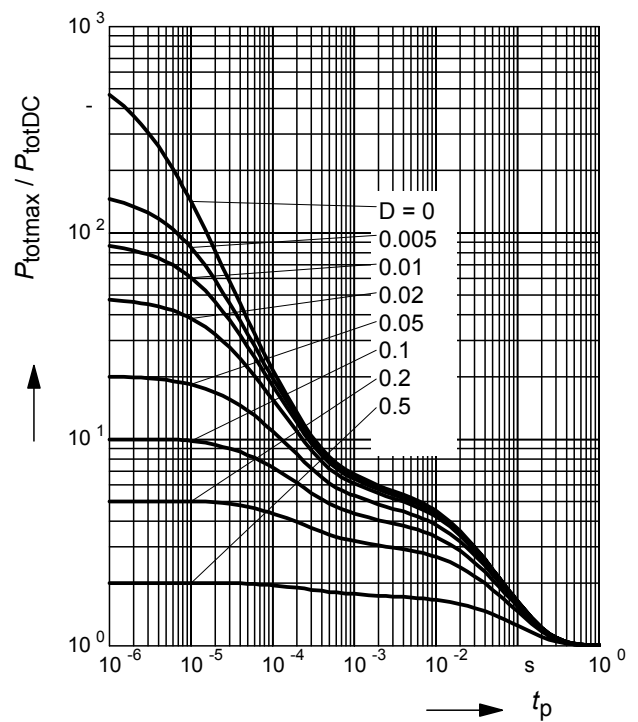
BCR191



Permissible Pulse Load

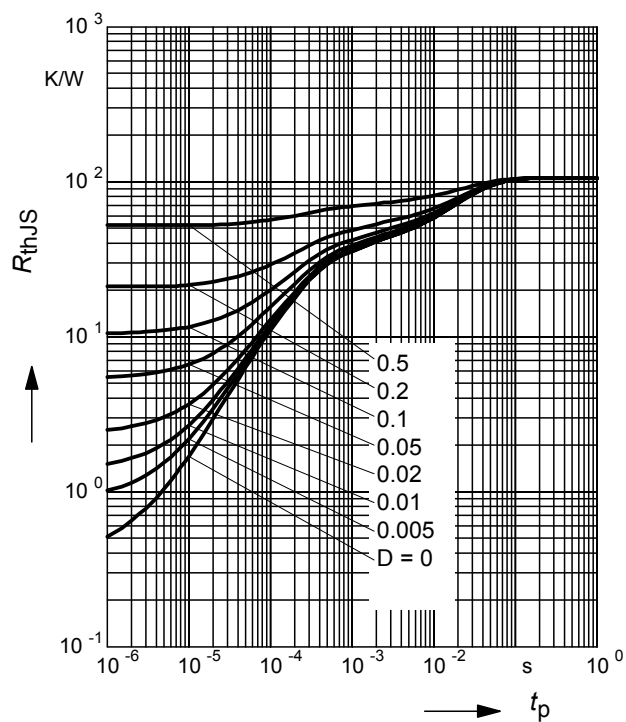
$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$

BCR191



Permissible Puls Load $R_{thJS} = f(t_p)$

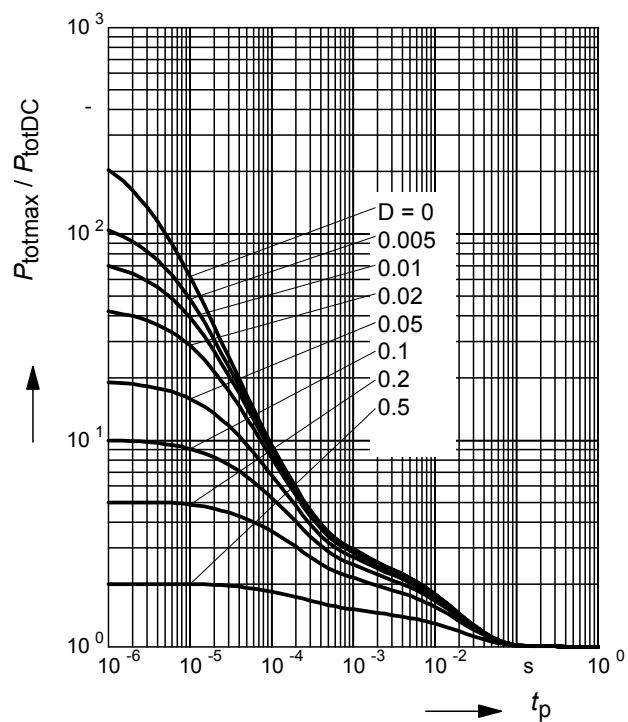
BCR191W

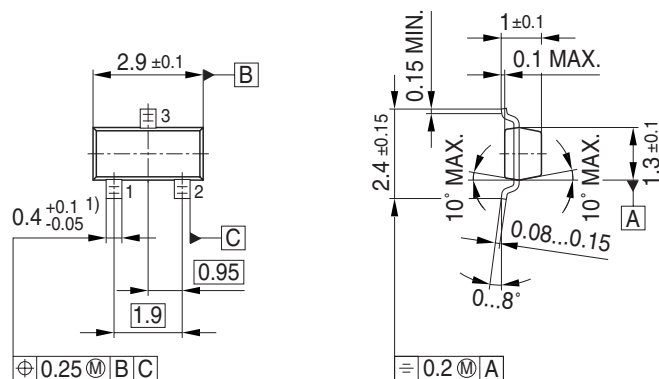


Permissible Pulse Load

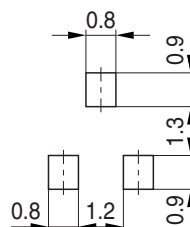
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR191W



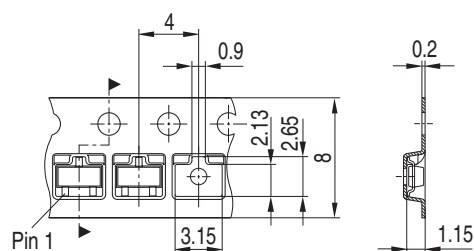


Foot Print

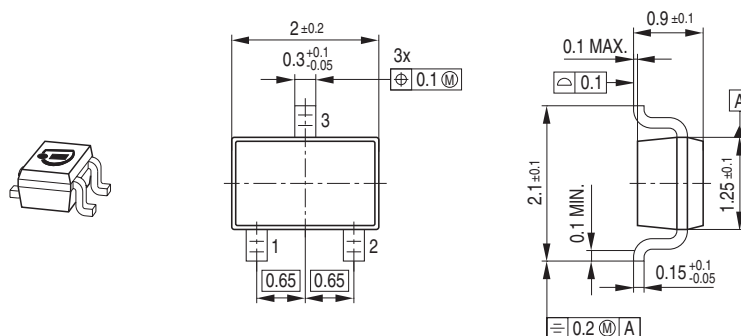


The diagram shows a top-down view of a BCW66 LED package. It is a rectangular component with four pins. The top pin is labeled 'Pin 1'. The package has a central rectangular area with the text 'EH S' and '05 05' (representing the date code 2005, June). The Infineon logo is shown in the top right corner. Labels with leader lines point to the Infineon logo (Manufacturer), the date code (Date code (YM)), and the BCW66 text (Type code).

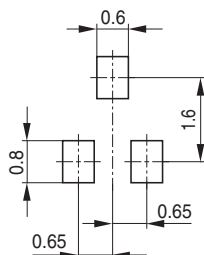
Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



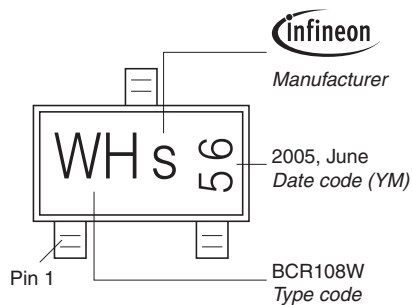
Package Outline



Foot Print

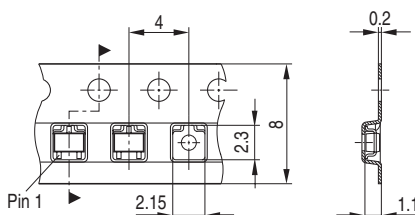


Marking Layout (Example)



Standard Packing

Reel $\varnothing 180$ mm = 3.000 Pieces/Reel
 Reel $\varnothing 330$ mm = 10.000 Pieces/Reel



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